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Circuit

(b) forming a second insulating layer with a second type of stress, different from said first type of stress;

(c) forming a conductive interconnection layer on and in contact with said second insulating layer; and

(d) forming a third insulating layer with said second type of stress on and in contact with said conductive interconnection layer.

34. A method according to claim 33 wherein said first type of stress is tensile stress and said second type of stress is compressive stress.

B  
cont.

35. A method according to claim 34 wherein said forming of said second insulating layer is by plasma CVD and said forming of said first insulating layer is by heating a gaseous mixture including an organic silane and oxygen to cause the oxygen to react with the organic silane.

36. A method according to claim 33 wherein aluminum conductors form said conductive interconnection layer.

→ 37. A semiconductor device comprising a substrate, a plurality of insulating films having different first and second types of stress formed on said substrate and a layer of conductive interconnectors sandwiched between and in contact with insulating films having the same type of stress.